

N-channel 100 V, 0.02 Ω typ., 32 A, STripFET™ F7 Power MOSFET in a DPAK package

Datasheet - production data

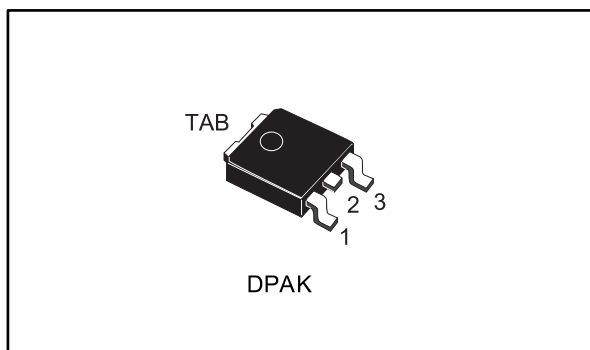
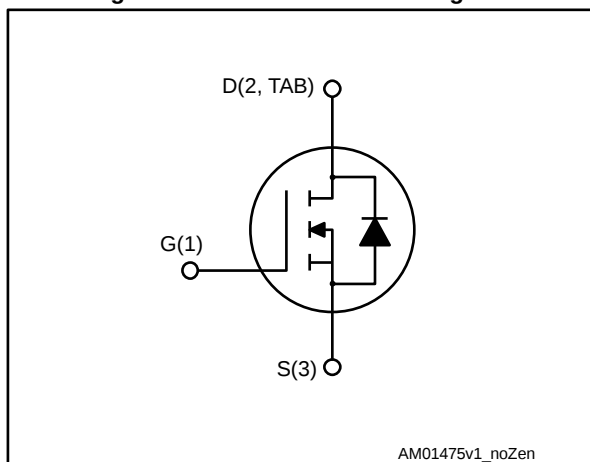


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STD30N10F7	100 V	0.024 Ω	32 A	50 W

- Among the lowest R_{DS(on)} on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STD30N10F7	30N10F7	DPAK	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	32	A
	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	23	
$I_{DM}^{(1)}$	Drain current (pulsed) at $T_C = 25\text{ }^{\circ}\text{C}$	132	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	50	W
T_J	Operating junction temperature range	-55 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		$^{\circ}\text{C}$

Notes:

⁽¹⁾Pulse width is limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	3	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	

Notes:

⁽¹⁾When mounted on a 1-inch² FR-4, 2 Oz copper board.

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 250 µA	100			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 100 V			1	µA
		V _{GS} = 0 V, V _{DS} = 100 V, T _C = 125 °C ⁽¹⁾			100	
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±20 V			100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 µA	2.5		4.5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 16 A		0.02	0.024	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0 V	-	1270	-	pF
C _{oss}	Output capacitance		-	290	-	pF
C _{rss}	Reverse transfer capacitance		-	24	-	pF
Q _g	Total gate charge	V _{DD} = 50 V, I _D = 32 A, V _{GS} = 0 to 10 V (see Figure 14: "Test circuit for gate charge behavior")	-	19	-	nC
Q _{gs}	Gate-source charge		-	9	-	nC
Q _{gd}	Gate-drain charge		-	4.5	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 16 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 13: "Test circuit for resistive load switching times" and Figure 18: "Switching time waveform")	-	12	-	ns
t _r	Rise time		-	17.5	-	ns
t _{d(off)}	Turn-off delay time		-	22	-	ns
t _f	Fall time		-	5.6	-	ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 32\text{ A}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 32\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 80\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	41		ns
Q_{rr}	Reverse recovery charge		-	47		nC
I_{RRM}	Reverse recovery current		-	2.3		A

Notes:

⁽¹⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

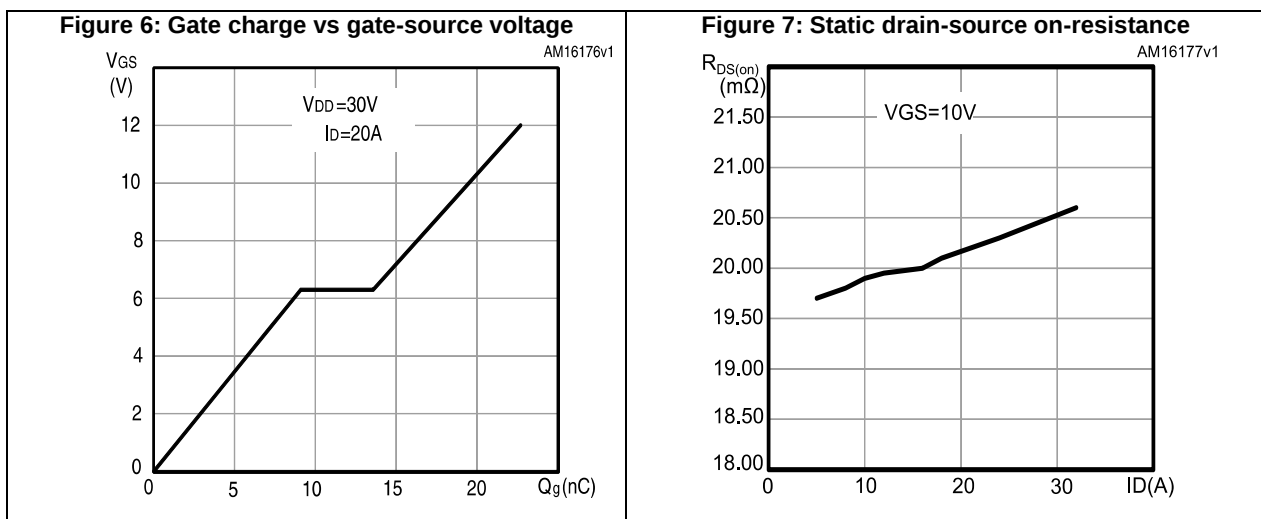
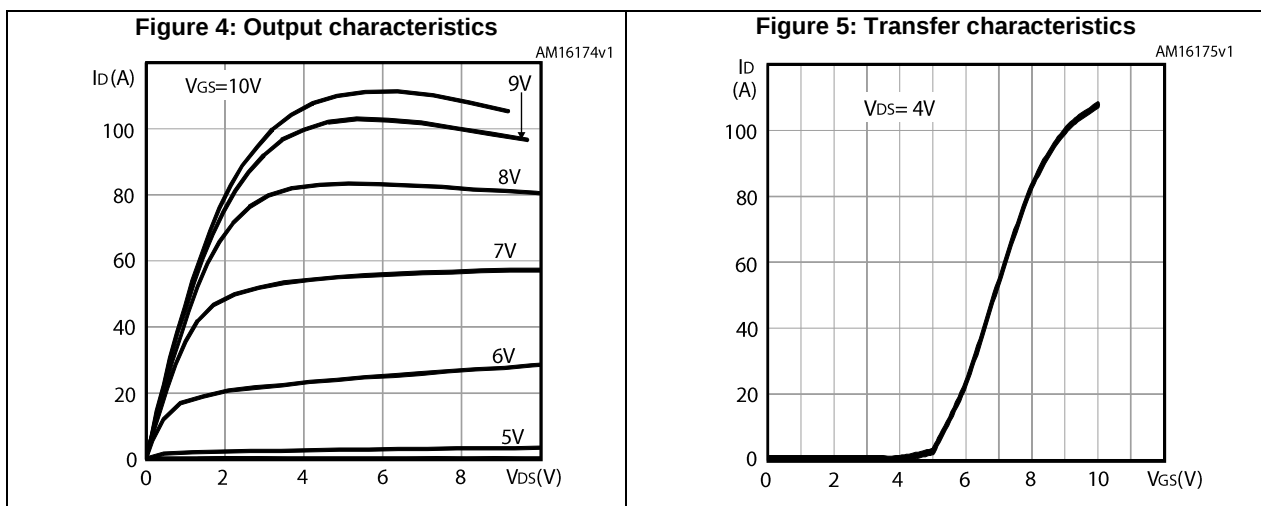
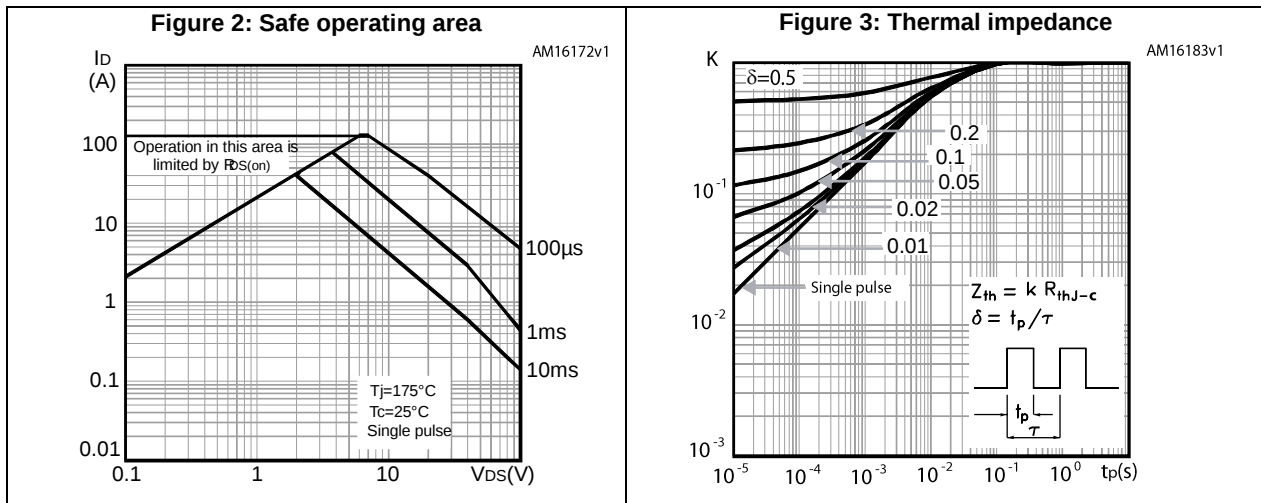


Figure 8: Capacitance variations

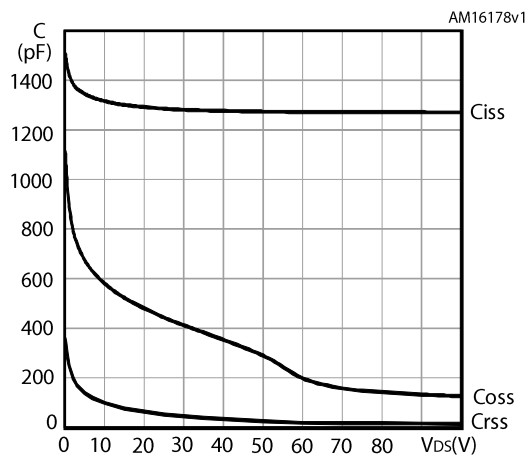


Figure 9: Normalized gate threshold voltage vs temperature

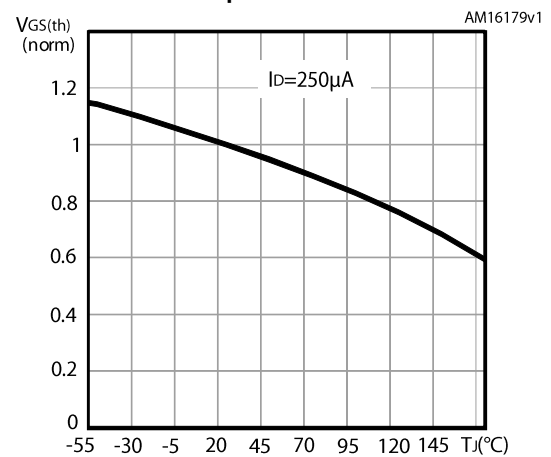


Figure 10: Normalized on-resistance vs temperature

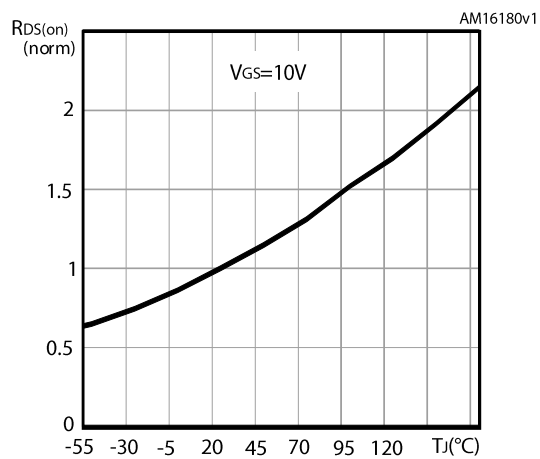
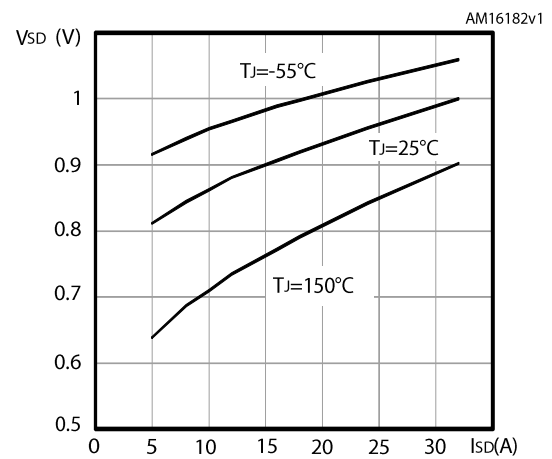
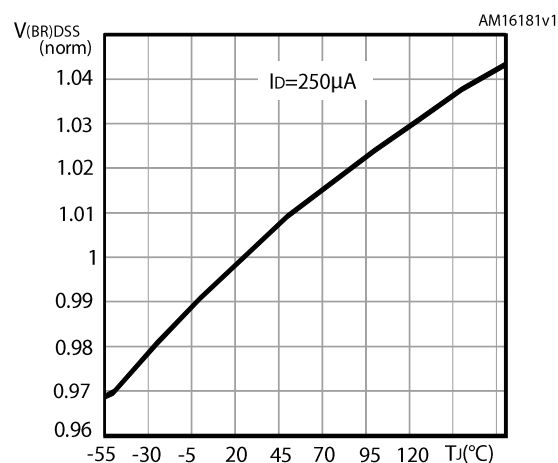


Figure 11: Source-drain diode forward characteristics

Figure 12: Normalized $V_{(BR)DSS}$ vs temperature

3 Test circuits

Figure 13: Test circuit for resistive load switching times



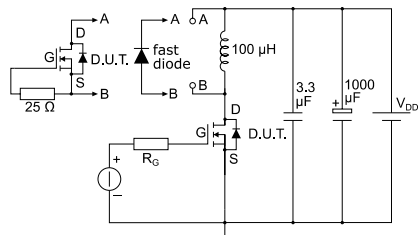
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Figure 14: Test circuit for gate charge behavior



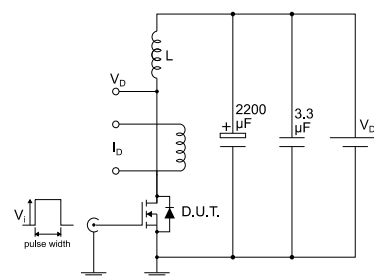
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Figure 15: Test circuit for inductive load switching and diode recovery times



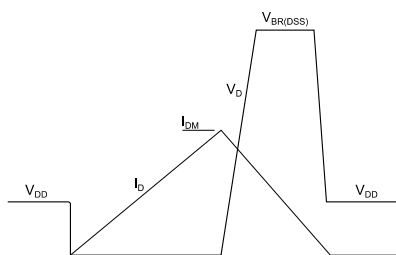
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Figure 16: Unclamped inductive load test circuit



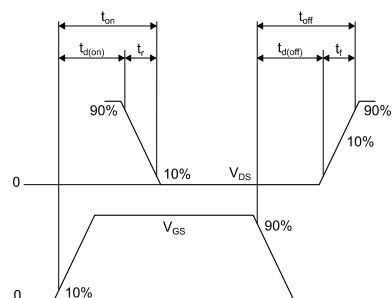
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 19: DPAK (TO-252) type A package outline

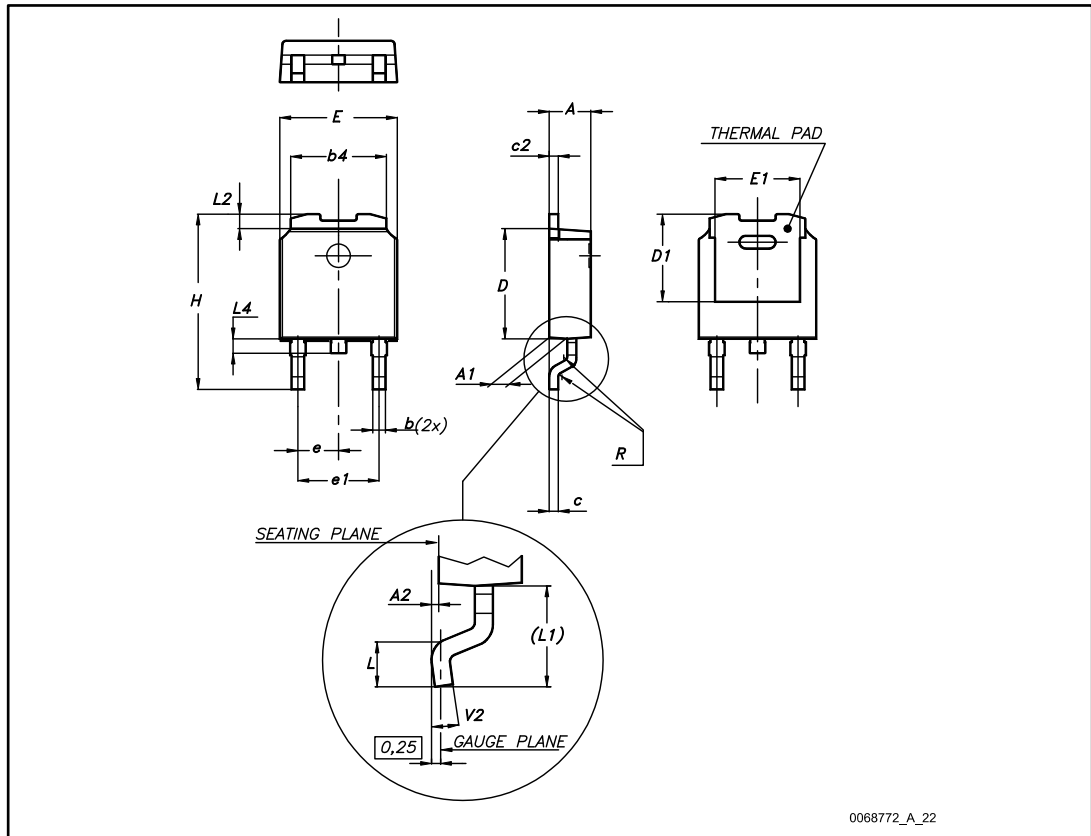
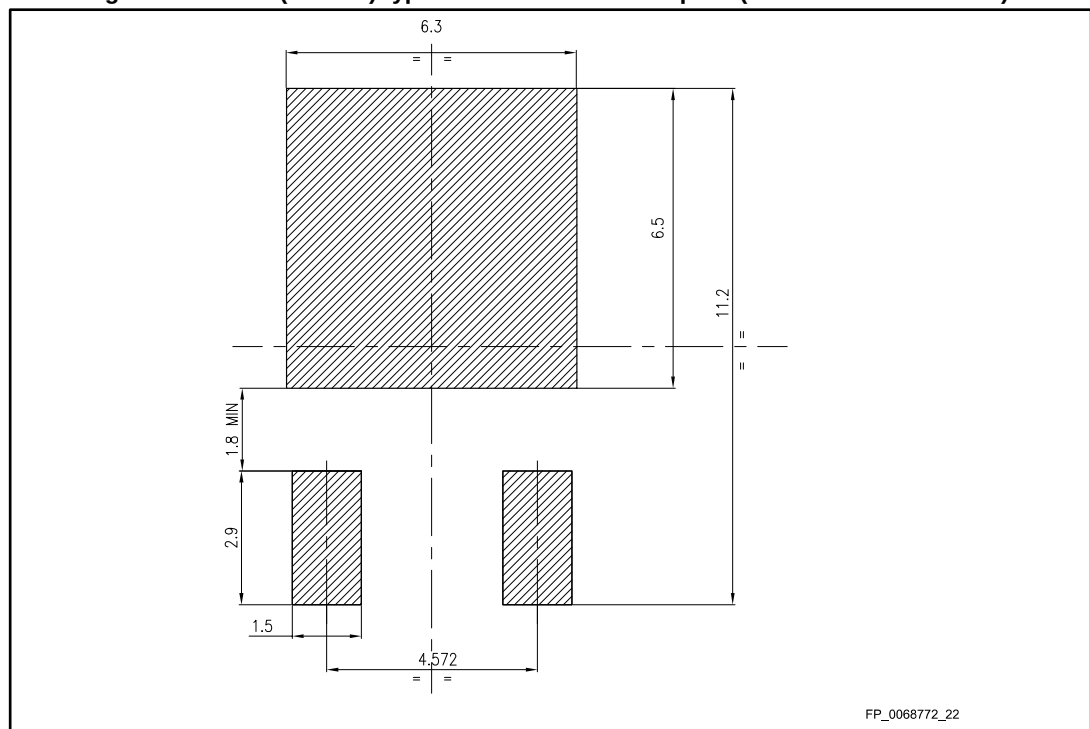


Table 8: DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20: DPAK (TO-252) type A recommended footprint (dimensions are in mm)



4.2 DPAK (TO-252) packing information

Figure 21: DPAK (TO-252) tape outline

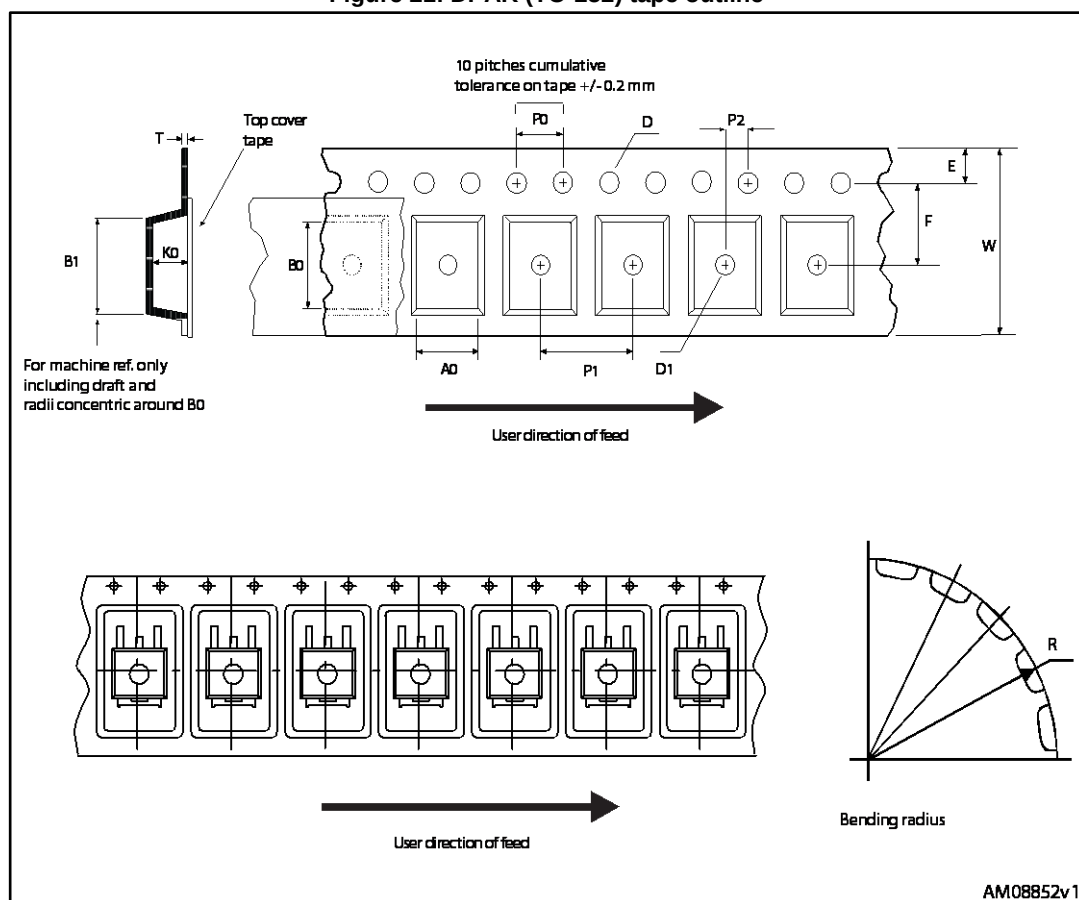


Figure 22: DPAK (TO-252) reel outline

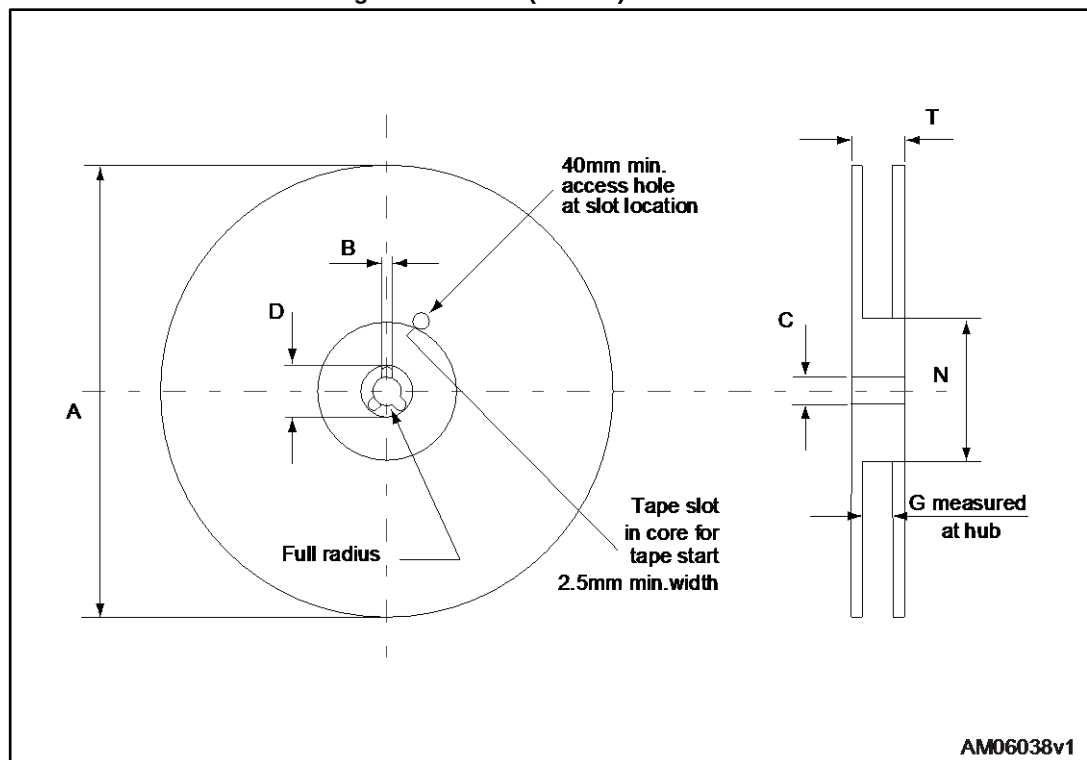


Table 9: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
28-Nov-2013	1	First release
03-Apr-2014	2	– Updated: <i>Figure 13,14,15</i> and <i>Figure 16</i> – Updated: <i>Section 4.1: DPAK, STD30N10F7</i> – Minor text changes.
27-Jan-2016	3	– Updated title – Updated <i>Section 2: Electrical characteristics</i> – Updated <i>Section 4: Package information</i> – Minor text changes.
16-May-2017	4	Modified Table 2: "Absolute maximum ratings" . Updated Section 4: "Package information" . Minor text changes.

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